

Amendments to the CLAIMS

1. (Original) A high frequency circuit characterized by comprising:
a plurality of shunt paths including active elements and impedance elements in between a high frequency transmission path and a ground, said active element being comprised of a field effect transistor serially connected between two capacitors;
wherein said plurality of shunt circuits ~~form~~ provide a parallel resonance circuit of said impedance elements when each of said active elements is ON, and a serial resonance circuit of said impedance elements when each of said active elements is OFF.
2. (Cancelled)
3. (Cancelled)
4. (Cancelled)
5. (Cancelled)
6. (New) A high frequency circuit comprising:
a plurality of shunt paths, including active elements and impedance elements, between a high frequency transmission path and a ground, said active element being comprised of a transistor serially connected between two capacitors;
wherein said plurality of shunt circuits provides a parallel resonance circuit, including said impedance elements when each of said active elements is in a first state, and a serial resonance circuit including said impedance elements when each of said active elements is in a second state.

7. (New) The high frequency circuit according to claim 6, wherein said transistor is a field effect transistor.

8. (New) The high frequency circuit according to claim 7, wherein said field effect transistor is made of gallium arsenic series material.

9. (New) The high frequency circuit according to claim 6, wherein said plurality of shunt paths are formed on a same substrate.

10. (New) The high frequency circuit according to claim 6, wherein at least one of said plurality of shunt paths includes an inductor.

11. (New) The high frequency circuit according to claim 6, wherein at least one of said shunt paths includes one of said active elements in series with an inductor, and at least one of said shunt paths includes one of said active elements in parallel with an inductor.

12. (New) The high frequency circuit according to claim 11, wherein:

said at least one said shunt paths including one of said active elements in parallel with said inductor, further comprises a capacitor in series with both one of said active elements and said inductor; and

said at least one said shunt paths including one of said active elements in series with said inductor, includes said inductor in series between said active element and said ground.

13. (New) The high frequency circuit according to claim 6, wherein at least one of said shunt paths include one of said active elements in series with a capacitor, and at least one of said shunt paths include one of said active elements in parallel with a capacitor.

14. (New) The high frequency circuit according to claim 13, wherein:

said at least one said shunt paths including one of said active elements in parallel with said capacitor, further comprises an inductor in series with both one of said active elements and said capacitor; and

said at least one said shunt paths including one of said active elements in series with said capacitor, includes said capacitor in series between said active element and said ground.

15. (New) The high frequency circuit according to claim 6, wherein each of said plurality of shunt paths includes inductive elements formed from components of an IC bonding wire.

16. (New) The high frequency circuit according to claim 6, wherein:

said parallel resonance circuit includes a plurality of inductors; and

said serial resonance circuit includes a single inductor.

17. (New) The high frequency circuit according to claim 6, wherein each of said shunt paths further includes an inductor, said inductor being positioned between said active element and said ground.

18. (New) A high frequency circuit comprising:

at least one pair of shunt paths, each shunt path in each pair of shunt paths, including an active element and an impedance element located between a high frequency transmission path and a ground, said active element being comprised of a transistor serially connected between two capacitors;

wherein, when each of said active elements is in a first state, each pair of shunt paths provides a parallel resonance circuit from said high frequency transmission path and said ground, including said impedance element from each shunt path; and

wherein, when each of said active elements is in a second state, each pair of shunt paths provides a serial resonance circuit from said high frequency transmission path and said ground, including said impedance element from each of said pair of shunt paths.